描述 / Descriptions

TO-251 塑封封装 双向可控硅。Triac in a TO-251 Plastic Package.

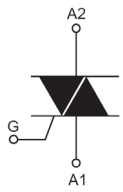
特征 / Features

中电流可控硅，低通态压降，高可靠性和稳定性，热敏电阻特性低。
Medium current triac, Low on state voltage drop,High reliability and stability, Low thermal resistance.

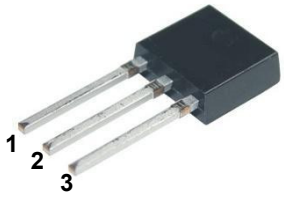
用途 / Applications

适用于一般用途交流开关。如固态继电器、加热调节、异步电动机起动电路、电机速度控制器等。
Suitable for general purpose AC switching .Such as static relays,heating regulation,induction motor starting circuits,motor speed controllers,etc.

内部等效电路 / Equivalent Circuit



引脚排列 / Pinning



PIN1：Main Terminal 1　　PIN 2：Main Terminal 2　　PIN 3：Gate

放大及印章代码 / h_{FE} Classifications & Marking

见印章说明。See Marking Instructions.

极限参数 / Absolute Maximum Ratings(Ta=25℃)

参数 Parameter	符号 Symbol	数值 Rating	单位 Unit
Repetitive peak off-state voltages	V_{DRM}/V_{RRM}	600 and 800	V
RMS on-state current(full sine wave T_C=105℃)	$I_{T(RMS)}$	8.0	A
Non repetitive surge peak on-state current(full cycle, T_j initial=25°C)	$I_{TSM(F=50Hz\ t=20ms)}$	80	A
Non repetitive surge peak on-state current(full cycle, T_j initial=25°C)	$I_{TSM(F=60Hz\ t=16.7ms)}$	84	A
I^2t Value for fusing	$I^2t_{(tp=10ms)}$	36	A^2s
Critical rate of rise of on-state current I_G =2xI_{GT} t_r ≤100 ns（F=120Hz T_j=125℃）	dI/dt	50	A/μs
Peak gate current(t_p =20μs T_j=125℃)	I_{GM}	4.0	A
Average gate power dissipation(T_j=125℃)	$P_{G(AV)}$	1.0	W
Operating junction temperature range	T_j	-40～125	℃
Storage junction temperature range	T_{stg}	-40～150	℃
Junction to ambient	$R_{th(j-a)}$	60	℃/W
Junction to case (AC)	$R_{th(j-c)}$	2.5	℃/W

电性能参数 / Electrical Characteristics(Ta=25℃)

免缓冲器和逻辑电平（3象限） / Snubberless and logic level (3 quadrants)

符号 Symbol	测试条件 Test Conditions	信号区 Quadrant		BTB08I				单位 Unit
				TW	SW	CW	BW	
I_{GT}(1)	V_D=12V R_L=30Ω	I-II-III	Max.	5	10	35	50	mA
V_{GT}	V_D=12V R_L=30Ω	I-II-III	Max.	1.3				V
V_{GD}	V_D=V_{DRM} R_L=3.3KΩ T_j=125℃	I-II-III	Min.	0.2				V
I_H(2)	I_T=100mA		Max.	10	15	35	50	mA
I_L	I_G=1.2I_{GT}	I-III	Max.	10	25	50	70	mA
		II		15	30	60	80	
(dV/dt)(2)	V_D=67% V_{DRM} gate open T_j=125℃		Min.	20	40	400	1000	V/μs
(dI/dt)c(2)	(dV/dt)c=0.1V/μs T_j=125℃		Min.	3.5	5.4	-	-	A/m s
	(dV/dt)c=10V/μs T_j=125℃		Min.	1.5	2.98	-	-	
	Without snubber T_j=125℃		Min.	-	-	4.5	7	

Note 1：minimum I_{GT} is guaranted at 5% of I_{GT} max.
Note 2：for both polarities of A2 referenced to A1.

电性能参数 / Electrical Characteristics(Ta=25℃)

标准（4象限） / Standard（4 quadrants)

符号 Symbol	测试条件 Test Conditions	信号区 Quadrant		BTB08I C	BTB08I B	单位 Unit
I_{GT}(1)	V_D=12V R_L=30Ω	I-II-III IV	Max.	25 50	50 100	mA
V_{GT}	V_D=12V R_L=30Ω	ALL	Max.	1.3		V
V_{GD}	V_D=V_{DRM} R_L=3.3KΩ T_j=125℃	ALL	Min.	0.2		V
I_H(2)	I_T=500mA		Max.	25	50	mA
I_L	I_G=1.2I_{GT}	I-III- IV	Max.	40	50	mA
		II		80	100	
(dV/dt)(2)	V_D=67% V_{DRM} gate open T_j=125℃		Min.	200	400	V/μs
(dV/dt)c(2)	(dI/dt)c=5.3A/ms T_j=125℃		Min.	5.0	10	

Note 1：minimum I_{GT} is guaranted at 5% of I_{GT} max.
Note 2：for both polarities of A2 referenced to A1.

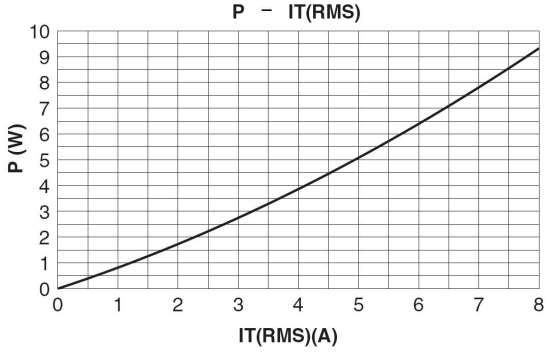
电性能参数 / Electrical Characteristics(Ta=25℃)

符号 Symbol	测试条件 Test Conditions			数值 Value	单位 Unit
V_{TM}(2)	I_{TM}=11A t_p =380μs T_j=25℃		Max.	1.55	V
V_{to}(2)	Threshold voltage T_j=125℃		Max.	0.85	V
R_d(2)	Dynamic resistance T_j=125℃		Max.	50	mΩ
I_{DRM} I_{RRM}	V_{DRM} = V_{RRM}	T_j=25℃	Max.	5.0	μA
		T_j=125℃	Max.	1.0	mA

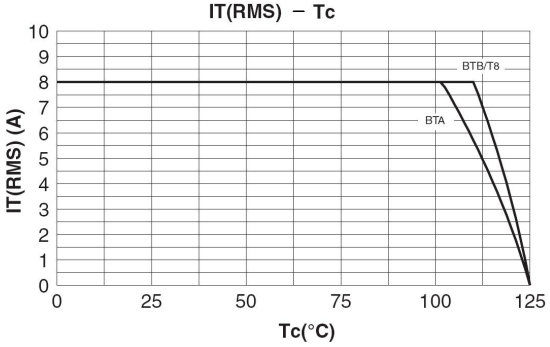
Note 2：for both polarities of A2 referenced to A1.

电参数曲线图 / Electrical Characteristic Curve

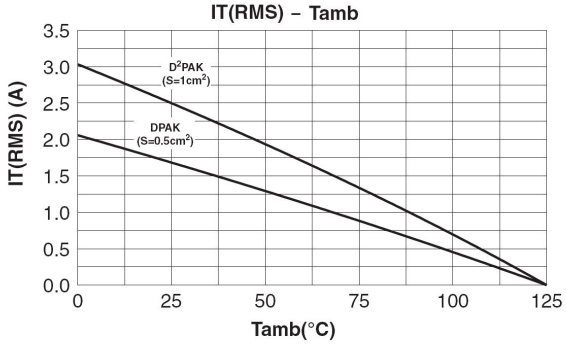
P – IT(RMS)



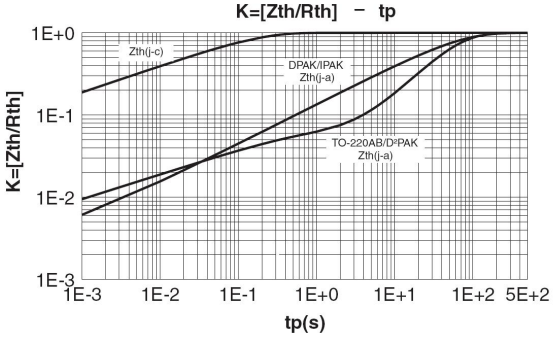
IT(RMS) – Tc



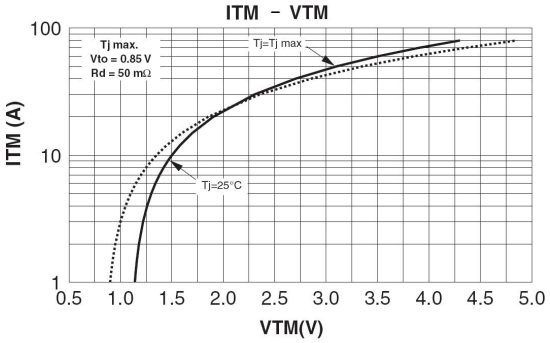
IT(RMS) – Tamb

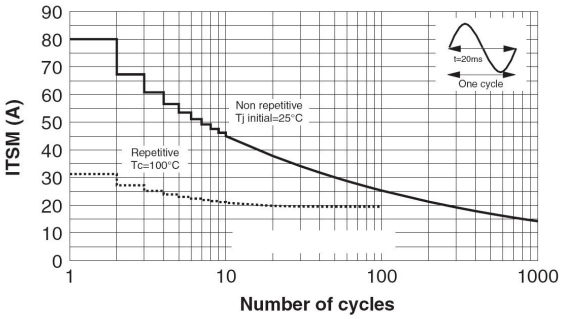


K=[Zth/Rth] – tp



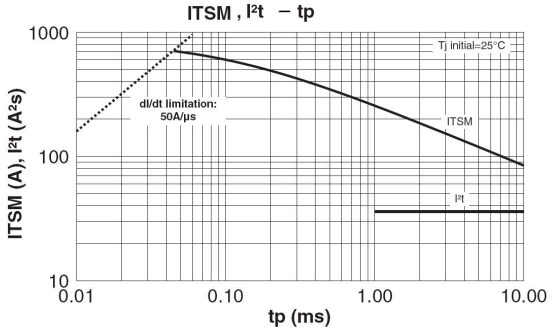
ITM – VTM



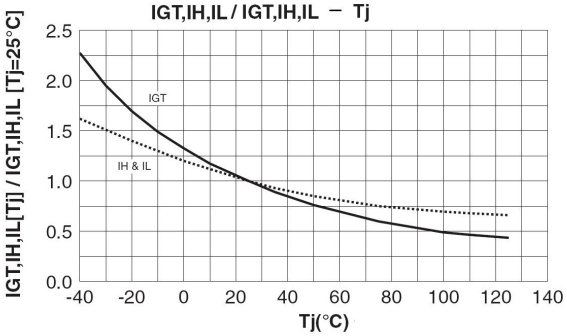


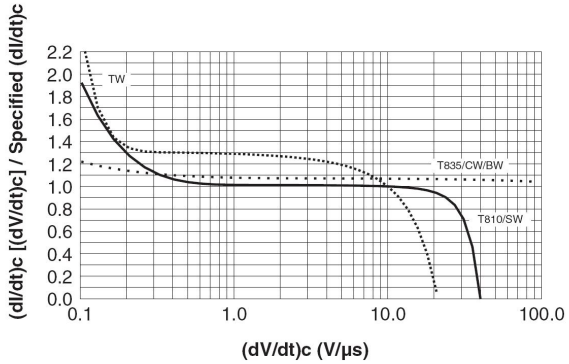
电参数曲线图 / Electrical Characteristic Curve

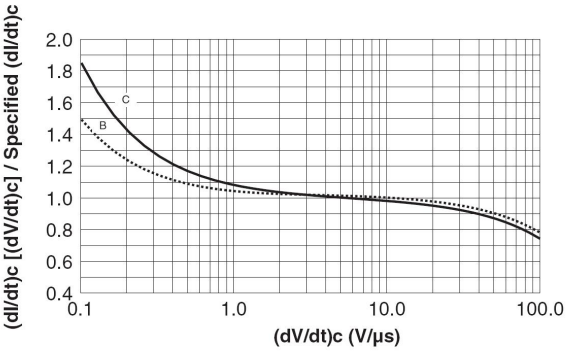
ITSM , I²t – tp

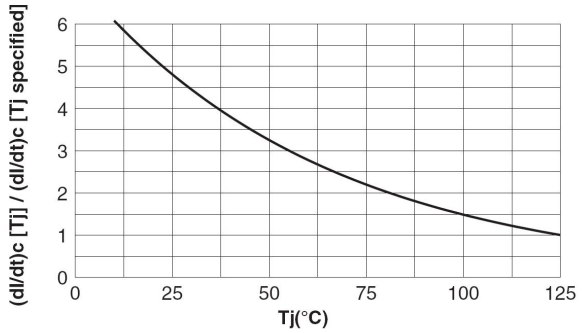


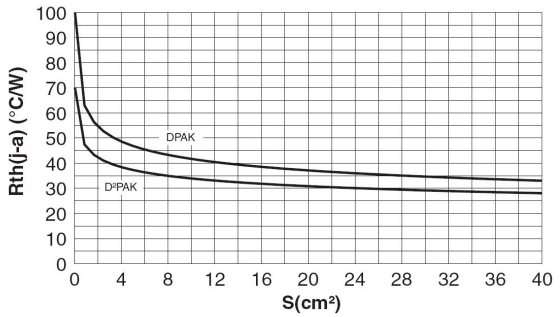
IGT,IH,IL / IGT,IH,IL – Tj



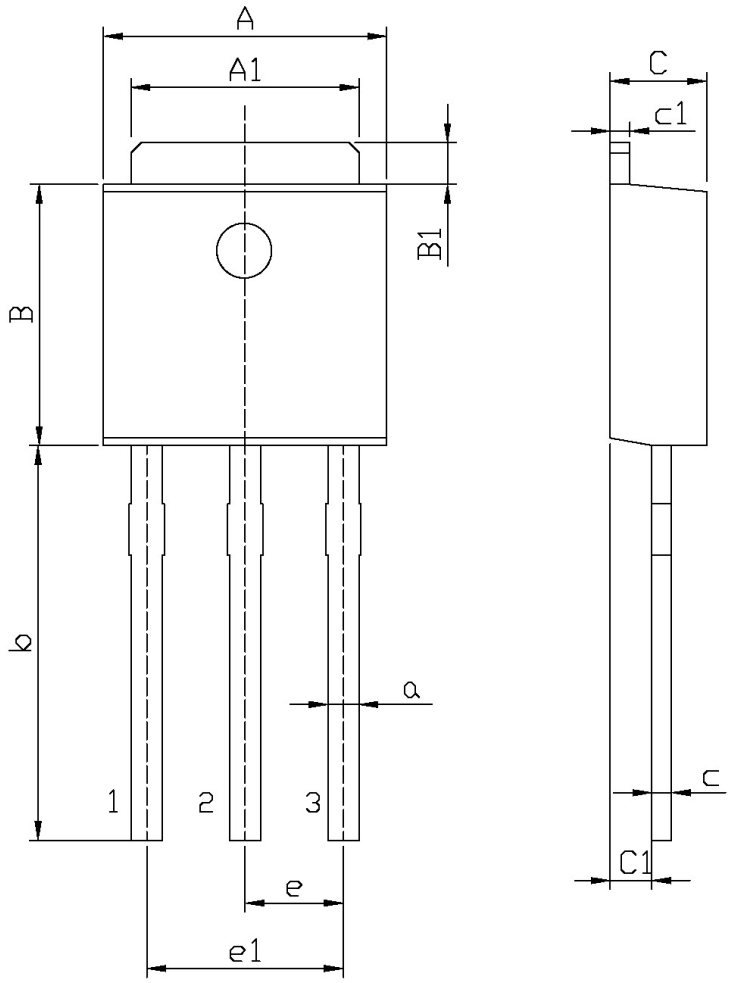








外形尺寸图 / Package Dimensions

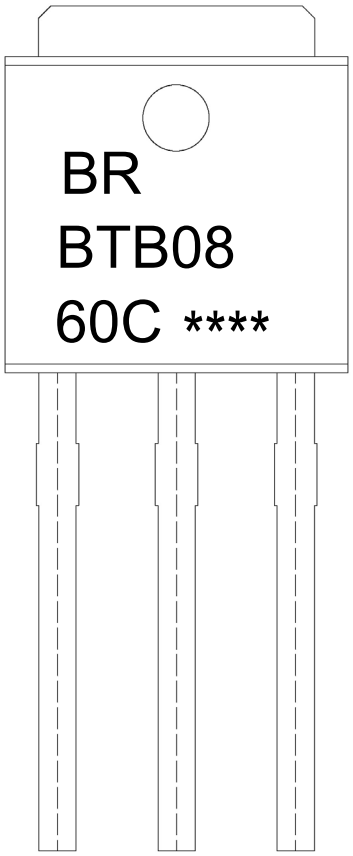


单位：mm

Symbol	Dimensions In Millimeters		Symbol	Dimensions In Millimeters	
	Min	Max		Min	Max
A	6.45	6.75	a	0.50	0.70
A1	5.10	5.50	b	9.00	9.40
B	5.95	6.25	c	0.45	0.55
B1	0.95	1.25	c1	0.45	0.55
C	2.20	2.40	e	2.24	2.34
C1	0.95	1.15	e1	4.43	4.73

TO-251

印章说明 / Marking Instructions



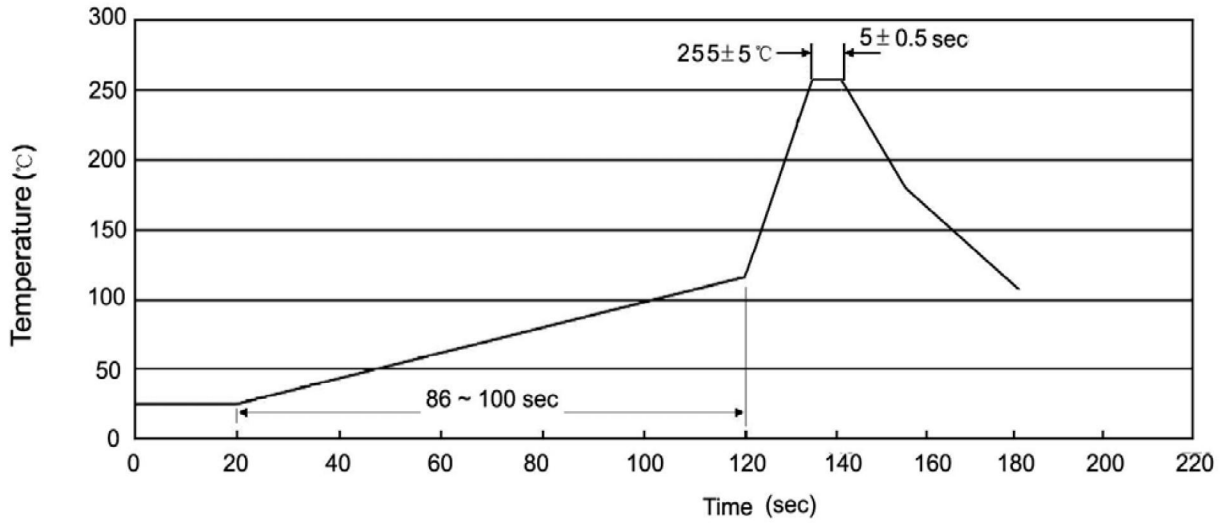
说明：

BR：	为公司代码
BTB08：	为产品型号
60C:	为 V_{RRM} 和 I_{GT} 分档代码
****：	为生产批号代码，随生产批号变化。

Note:

BR:	Company Code
BTB08:	Product Type.
60C:	V_{RRM}、I_{GT} Bracket code
****:	Lot No. Code, code change with Lot No.

波峰焊温度曲线图(无铅) / Temperature Profile for Dip Soldering(Pb-Free)



说明：

1、预热温度 25～150℃，时间 60～90sec;

2、峰值温度 255±5℃，时间持续为 5±0.5sec;

3、焊接制程冷却速度为 2～10℃/sec.

Note:

1.Preheating:25~150℃, Time:60~90sec.

2.Peak Temp.:255±5℃, Duration:5±0.5sec.

3. Cooling Speed: 2~10℃/sec.

耐焊接热试验条件 / Resistance to Soldering Heat Test Conditions

温度：270±5℃　　时间：10±1 sec.　　Temp.:270±5℃　　Time:10±1 sec

包装规格 / Packaging SPEC.

散件包装 / BULK

Package Type 封装形式	Units 包装数量					Dimension 包装尺寸 (unit: mm³)		
	Units/Bag 只/袋	Bags/Inner Box 袋/盒	Units/Inner Box 只/盒	Inner Boxes/Outer Box 盒/箱	Units/Outer Box 只/箱	Bag 袋	Inner Box 盒	Outer Box 箱
TO-251	1,000	10	10,000	5	50,000	135×190	237×172×102	560×245×195

套管包装 / TUBE

Package Type 封装形式	Units 包装数量					Dimension 包装尺寸 (unit: mm³)		
	Units/Tube 只/套管	Tubes/Inner Box 套管/盒	Units/Inner Box 只/盒	Inner Boxes/Outer Box 盒/箱	Units/Outer Box 只/箱	Tube 套管	Inner Box 盒	Outer Box 箱
TO-251/252	75	48	3,600	5	18,000	526×20.5×5.25	555×164×50	575×290×180

使用说明 / Notices